

LOWCOST-IC

LOWCOSTINTERCONNECTSWITHHIGHLYIMPROVEDCONTACT STRENGTH FOR SOC APPLICATIONS



| | |
|---|---|
| Project ID: | 826323 |
| PRD 2023: | Panel 7 – supply chain |
| Call topic: | FCH-02-6-2018: Cost-effective novel architectures of interconnects |
| Project total costs: | EUR 2 335 997.50 |
| Clean H₂ JU max. contribution: | EUR 2 335 997.50 |
| Project period: | 1.1.2019–30.9.2022 |
| Coordinator: | Danmarks Tekniske Universitet (DTU), Denmark |
| Beneficiaries: | Sandvik Materials Technology AB, Aperam Stainless France SA, AVL List GmbH, Borit NV, Chalmers Tekniska Högskola AB, Forschungszentrum Jülich GmbH, SolydEra SpA, Sunfire GmbH, Tecno Italia SRL |
| http://www.lowcost-ic.eu/ | |

PROJECT AND OBJECTIVES

The overall objective of LOWCOST-IC is to contribute to the successful upscaling of the widespread commercialisation of solid oxide cell (SOC) technologies by:

- increasing the robustness of the lifetime of SOC stacks by developing novel highly robust air electrode contact layers and testing new interconnect coatings in SOC stacks;
- minimising the interconnect development and production cost by introducing cheaper high-volume steel, applying state-of-the-art (SoA) large-scale roll-to-roll manufacturing methods for SOC manufacturing and developing a novel interconnect shape design process.

PROGRESS AND MAIN ACHIEVEMENTS

- Work package (WP) 2 aimed to reduce interconnect costs without affecting performance by exploring steel grades, coatings and manufacturing processes. The highlights are as follows:
 - roll-to-roll manufacturing – feasibility demonstrated, including shaping with hydroforming;
 - chromium evaporation – reduced by 30 times;
 - low-cost steels – comparable performance to specialised steel in terms of corrosion rate, chromium evaporation and area-specific resistance (ASR);
 - ASR of < 20 mΩcm² at 850 °C after 3 000 hours of operation achieved.
- In WP3, a new interconnect design with optimised flow distribution was developed, based on an efficient three-dimensional multiphysics

model considering flow, heat transfer, mechanical stresses and electrochemical reactions.

- In WP4, novel contact layers were developed by DTU, based on *in situ* reactive bonding, using metallic powders as precursors to form strong bonds through oxidation and reaction.
- In WP5, four stack designs were produced using different materials to demonstrate developed materials. A stack with Sanergy 441 HT interconnect steel-coating solution was tested for 3 500 hours at 800–850 °C. Sanergy HT 441 with CeCo coating showed more ASR degradation than Crofer 22 APU with MCF coating but performed better at lower temperature. A stack with the new contact layers performed similarly to standard solutions without optimisation.
- In WP6, the technical improvements converted into monetary values showing that the mass manufacturing routes would be commercially competitive compared with in-house production because of the scalable processes of roll-to-roll and high-speed printing.
- In WP7, the work was disseminated through 12 published papers, with 4 more in preparation; 11 conference presentations; and 2 workshops, each with 32 participants comprising academics and most of the SOC stack manufacturers in Europe.

FUTURE STEPS AND PLANS

- Stack modelling will continue in national and EU projects, e.g. the AMON project.
- The material development for contact layers will be paused due to lack of funding.
- A recommendation will be made to Hydrogen Europe to put more effort back into material research.

QUANTITATIVE TARGETS AND STATUS

| Target source | Parameter | Unit | Target | Achieved to date by the project | Target achieved? | SoA result achieved to date (by others) | Year for reported SoA result |
|--------------------------|----------------------------------|-------------------|--------|---------------------------------|------------------|---|------------------------------|
| Project's own objectives | Fracture energy of contact layer | J/m ² | 5.1 | 19.6 | ✓ | 1.7 | 2013 |
| | ASR of contact layer at 750 °C | mΩcm ² | 15 | 18 | ✓ | 15 | 2019 |
| | ASR of contact layer at 850 °C | mΩcm ² | 25 | 15 | ⚙️ | N/A | N/A |